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PATENT



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In ra Application of:	`	پر. ۱
In re Application of:	,	Examiner: C. Lee
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YOSHIMOBU SEKIGUCHI, et al.) .	Consess And I Inside 2002
A - 1 N - 10/500 170	:	Group Art Unit: 2892
Appl. No.: 10/566,170)	
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Int'l Filing Date: June 15, 2005)	
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§ 371(c) Date: January 27, 2006)	Certificate FEB 0 3 2009 of Correction
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For: SEMICONDUCTOR FILM)	25 v 3 2009
MANUFACTURING METHOD AND	. :	of Correction
SUBSTRATE MANUFACTURING)	- Juliacilou
METHOD	:	
)	
U.S. Patent No.: 7,399,693 B2	:	
)	
Issued: July 15, 2008	:	January 29, 2009
		.
Commissioner for Patents		
P.O. Box 1450		
Alexandria, VA 22313-1450		
,		

CERTIFICATE OF CORRECTION UNDER RULE 322

Sir:

It is respectfully requested that a Certificate of Correction be issued by the Patent and Trademark Office due to errors which appear in the printed patent as a result of Patent and Trademark Office mistakes. A Certificate of Correction form, in duplicate, is enclosed.

Patentees' undersigned attorney may be reached in our Costa Mesa,

California office by telephone at (714) 540-8700. All correspondence should be directed to our new address given below.

Respectfully submitted,

Damond E. Vadnais

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FITZPATRICK, CELLA, HARPER & SCINTO 30 Rockefeller Plaza
New York, New York 10112-3800
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FCHS_WS 2611799v1

UNITED STATES PATENT AND TRADEMARK OFFICE

CERTIFICATE OF CORRECTION

PATENT NO.

7,399,693 B2

DATED

July 15, 2008

INVENTOR(S) :

Yoshinobu Sekiguchi

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

COLUMN 12:

Line 57, "A1_{0.13}Ga_{0.87} layer 30:" should read -- A1_{0.13}Ga_{0.87} As layer 30: --.

COLUMN 16:

Line 25, "microc-" should read -- micro- --; and Line 26, "rystalline" should read -- crystalline --.

MAILING ADDRESS OF SENDER:

FITZPATRICK, CELLA, HARPER & SCINTO 30 Rockefeller Plaza New York, New York 10112-3800 (212) 218-2100 - Telephone (212) 218-2200 - Facsimile PATENT NO. 7,399,693 B2

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(Form#30) FCHSWS_2802079 \Rightarrow

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